NSN 5961-01-079-5632

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No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-079-5632 **Inclosure Material:** Ceramic and metal **Overall Length:** 0.800 inches **Overall Height:** 0.225 inches **Overall Width:** 0.750 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Base **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 26.0 breakdown voltage, collector-to-emitter, base open and 55.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter and 4.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 12.00 amperes source cutoff current **Power Rating Per Characteristic:** 97.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Test Data Document:** 19156-950031 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 tab, solder lug and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:**